

Effect of Annealing Treatment on Thermoelectric Properties of Ti-doped ZnO Thin Film



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Overview of magnetron sputtering

Ar Chamber high vacuum low vacuum 3.0 x 10<sup>-5</sup> T. 3.0 x 10<sup>-3</sup> T. ich MF Controller DC Power supply HV Gauge Annealing 373, 473 and 573 K

Magnetron sputtering is one of the physical vapor deposition (PVD) processes where ions are accelerated from plasma across a potential drop to bombard the sputtering target. These energetic incident ions cause the ejection of atoms from the target surface. The neutral particles will travel to the substrate which located near the target. They will condense to from a film. The various types of magnetron sputtering technique are direct current (dc), alternating current (ac), radio frequency (rf), and pulsed-dc.



## ZnTiO

## Measurement of thin film properties

